HRU0302A

Silicon Schottky Barrier Diode for Rectifying

HITACHI

ADE-208-235E(Z)
Rev 5
June 1996

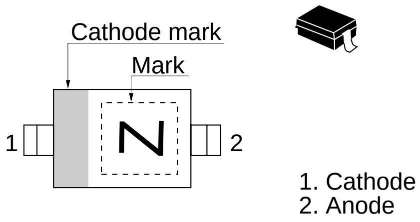
Features

- Low forward voltage drop and suitable for high effifiency forward current.
- Ultra small Resin Package (URP) is suitablefor high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HRU0302A	Z	URP

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	VRRM*1	20	V
Average rectified current	IO*2	300	mA
Non-Repetitive peak forward surge current	IFSM*3	3	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55Å`+125	°C

Notes 1. See Fig.4

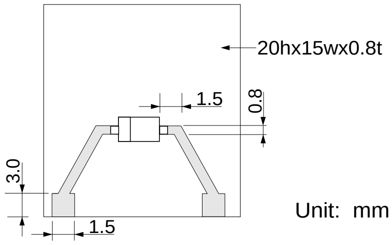
Notes 2. See Fig.5

sec half sine wave 1 pulse

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	VF	Å \	Å \	0.4	V	IF = 300 mA
Reverse current	IR	Å \	Å \	100	µA	VR = 20V
Capacitance	C	Å \	70	Å \	pF	VR = 0V, f = 1 MHz
Thermal resistance	Rth(j-a)	Å \	440	Å \	°C/W	Polyimide substrate*1

Notes 1. Polyimide PCB



Unit: mm

Main Characteristic

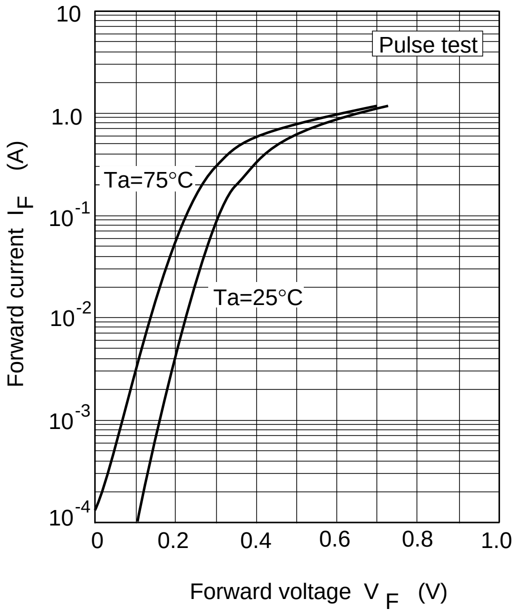


Fig.1 Forward current Vs. Forward voltage

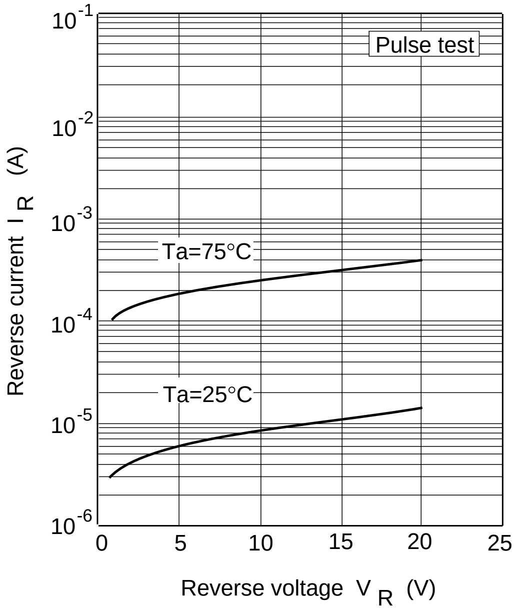


Fig.2 Reverse current Vs. Reverse voltage

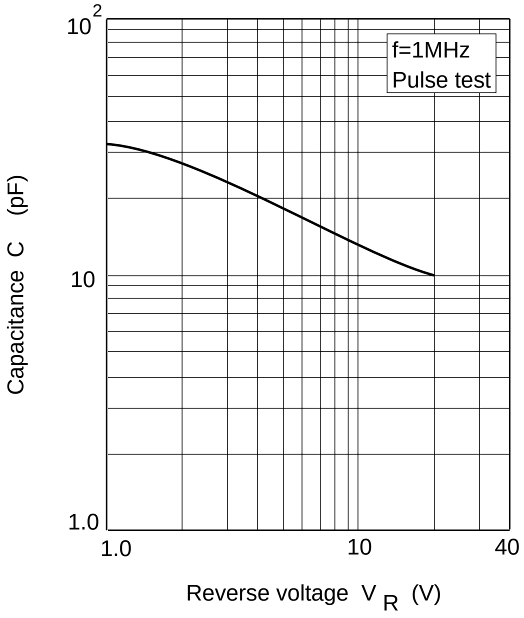


Fig.3 Capacitance Vs. Reverse voltage

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Main Characteristic

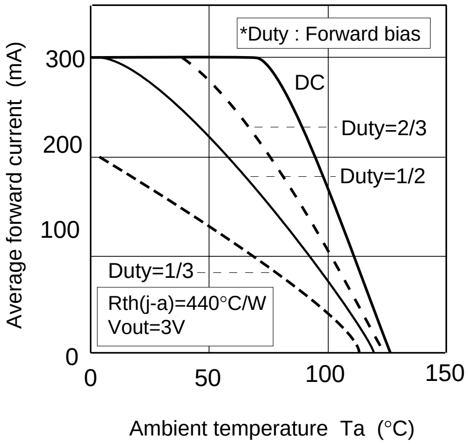

Fig.4 Average forward current Vs. Ambient temperature

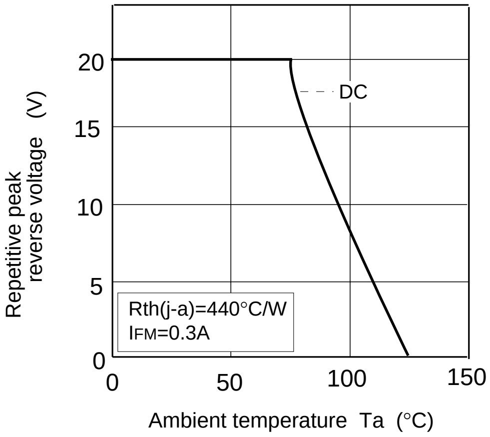

Fig.5 Repetitive peak reverse voltage Vs. Ambient temperature

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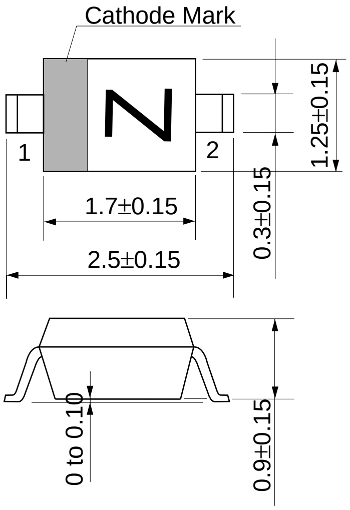
Package Dimensions

Unit : mm



1. Cathode
2. Anode

Hitachi Code	URP
JEDECCode	—
EIAJCode	—
Weight(g)	0.004